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## **FXLA0104**

# Low-Voltage Dual-Supply 4-Bit Voltage Translator with Configurable Voltage Supplies and Signal Levels, 3-State Outputs, and Auto Direction Sensing

#### **Features**

- Bi-Directional Interface between Two Levels: from 1.1 V to 3.6 V
- Fully Configurable: Inputs and Outputs Track V<sub>CC</sub>
- Non-Preferential Power-Up; Either V<sub>CC</sub> May Be Powered Up First
- Outputs Switch to 3-State if Either V<sub>CC</sub> is at GND
- Pow er-Off Protection
- Bus-Hold on Data Inputs Eliminates the Need for Pull-Up Resistors; Do Not Use Pull-Up Resistors on A or B Ports
- Control Input (OE) Referenced to V<sub>CCA</sub> Voltage
- Available in the 12-Lead, 1.7 mm x 2.0 mm UMLP Package
- Direction Control Not Necessary
- 100 Mbps Throughput when Translating Between
   1.8 V and 2.5 V
- ESD Protection Exceeds:
  - 6 kV HBM (per JESD22-A114 & Mil Std 883e 3015.7)
  - 2 kV CDM (per ESD STM 5.3)

## **Applications**

Cell Phone, PDA, Digital Camera, Portable GPS

## **Description**

The FXLA0104 is a configurable dual-voltage supply translator for both uni-directional and bi-directional voltage translation between two logic levels. The device allows translation between voltages as high as 3.6 V to as low as 1.1 V. The A port tracks the  $V_{\rm CCA}$  level and the B port tracks the  $V_{\rm CCB}$  level. This allows for bi-directional voltage translation over a variety of voltage levels: 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V.

The device remains in three-state as long as either  $V_{\text{CC}}$ =0V, allowing either  $V_{\text{CC}}$  to be powered up first. Internal power-down control circuits place the device in 3-state if either  $V_{\text{CC}}$  is removed.

The OE input, when LOW, disables both the A and B ports by placing them in a 3-state condition. The OE input is supplied by  $V_{\text{CCA}}$ .

The FXLA0104 supports bi-directional translation without the need for a direction control pin. The two ports of the device have auto-direction sense capability. Either port may sense an input signal and transfer it as an output signal to the other port.

## **Ordering Information**

Part Number	Operating Temperature Range	Top Mark	Package	Packing Method
FXLA0104QFX	-40 to 85°C	XU	12-Lead, 1.7 mm x 2.0 mm Ultrathin Molded Leadless Package (UMLP)	5000 Units Tape and Reel

# **Pin Configuration**

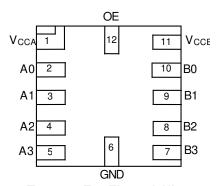
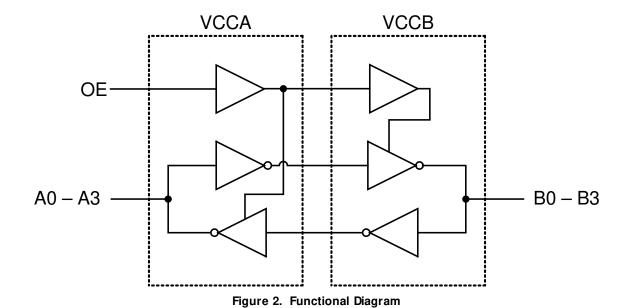


Figure 1. Top Through View

## **Pin Definitions**

Pin#	Name	Description
1	V <sub>CCA</sub>	A-Side Pow er Supply
2	A0	A-Side Inputs or 3-State Outputs
3	A1	A-Side Inputs or 3-State Outputs
4	A2	A-Side Inputs or 3-State Outputs
5	A3	A-Side Inputs or 3-State Outputs
6	GND	Ground
7	B3	B-Side Inputs or 3-State Outputs
8	B2	B-Side Inputs or 3-State Outputs
9	B1	B-Side Inputs or 3-State Outputs
10	В0	B-Side Inputs or 3-State Outputs
11	V <sub>CCB</sub>	B-Side Pow er Supply
12	OE	Output Enable Input

# **Functional Diagram**



**Function Table** 

Control	Outputs
OE	- Ca.pa.o
LOW Logic Level	3-State
HIGH Logic Level	Normal Operation

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Condition	Min.	Max.	Unit
Vcc	Supply Voltage	Vcca	-0.5	4.6	V
V CC	Supply Vollage	V <sub>CCB</sub>	-0.5	4.6	V
Vı	DC Input Voltage	VO Ports A and B	-0.5	4.6	V
V 1	DO Input Voltage	Control Input (OE)	-0.5	4.6	V
		Output 3-State	-0.5	4.6	
Vo	Output Voltage <sup>(2)</sup>	Output Active (An)	-0.5	V <sub>CCA</sub> +0.5	V
		Output Active (B <sub>n</sub> )	-0.5	V <sub>CCB</sub> +0.5	
l <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> <0V		-50	mA
lok	DC Output Diode Current	Vo<0V		-50	mA
IOK	Do Output Diode Current	V <sub>O</sub> >V <sub>CC</sub>		+50	ША
lon/lol	DC Output Source/Sink Curre	ent	-50	+50	mA
lcc	DC V <sub>CC</sub> or Ground Current (p	per Supply Pin)		±100	mA
T <sub>STG</sub>	Storage Temperature Range		-65	+150	°C
P <sub>D</sub>	Pow er Dissipation			17	mW
ESD	Electrostatic Discharge	Human Body Model (per JESD22-A114 & Mil Std 883e 3015.7)		6	kV
	Capability	Charged Device Model (per ESD STM 5.3)		2	KV

#### Notes:

- 1. lo absolute maximum ratings must be observed.
- 2. All unused inputs and input/outputs must be held at V<sub>CCi</sub> or GND.

## **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Condition	Min.	Max.	Unit
V <sub>CC</sub>	Pow er Supply	Operating V <sub>CCA</sub> or V <sub>CCB</sub>	1.1	3.6	V
V <sub>IN</sub>	Input Voltage	Ports A and B	0	3.6	V
V IIV	Input Voltage	Control Input (OE)	0	$V_{CCA}$	V
TA	Operating Temperature, Free Air		-40	+85	°C
dt/dV	Minimum Input Edge Rate	$V_{CCA/B} = 1.1 \text{ to } 3.6 \text{ V}$		10	ns/V
ΘЈΑ	Thermal Resistance: Junction-to-Ambient			300	°C/W
Θυс	Thermal Resistance: Junction-to-Case			165	°C/W

## Power-Up/Power-Down Sequence

FXL translators offer an advantage in that either  $V_{\rm CC}$  may be powered up first. This benefit derives from the chip design. When either  $V_{\rm CC}$  is at 0V, outputs are in a high-impedance state. The control input (OE) is designed to track the  $V_{\rm CCA}$  supply.

The recommended power-up sequence is:

- 1. Apply power to the first V<sub>CC</sub>.
- 2. Apply power to the second  $V_{CC}$ .
- 3. Drive the OE input HIGH to enable the device.

The recommended power-down sequence is:

- 1. Drive OE input LOW to disable the device.
- 2. Remove power from either  $V_{\text{CC}}$ .
- 3. Remove power from other  $V_{\text{CC}}$ .

## Pull-Up/Pull-Down Resistors

<u>Do not use pull-up or pull-down resistors</u>. This device has bus-hold circuits: pull-up or pull-down resistors are not recommended because they interfere with the output state. The current through these resistors may exceed the hold drive,  $I_{\text{I}(\text{HOLD})}$  and/or  $I_{\text{I}(\text{OD})}$  bus-hold currents, resulting in data transition and/or auto-direction sensing failures. The bus-hold feature eliminates the need for extra resistors.

## **DC Electrical Characteristics**

T<sub>A</sub>=-40 to 85°C

Symbol	Parameter	Condition	V <sub>CCA</sub> (V)	V <sub>CCB</sub> (V)	Min.	Тур.	Max.	Unit	
			2.70 to 3.60		2.00				
			2.30 to 2.70		1.60				
V <sub>IHA</sub>		Data Inputs An Control Pin OE	1.65 to 2.30	1.10 to 3.60	.65xV <sub>CCA</sub>			V	
		CONTROL LINE OF	1.40 to 1.65		.65xV <sub>CCA</sub>				
	High-Level Input		1.10 to 1.40		.90xV <sub>CCA</sub>				
	Voltage			2.70 to 3.60	2.00				
				2.30 to 2.70	1.60				
V <sub>IHB</sub>		Data Inputs Bn		1.65 to 2.30	.65xV <sub>CCB</sub>			V	
					.65xV <sub>CCB</sub>				
				1.10 to 1.40	.90xV <sub>CCB</sub>				
			2.70 to 3.60				.80		
			2.30 to 2.70				.70		
VILA		Data Inputs An Control Pin OE	1.65 to 2.30	1.10 to 3.60			.35xV <sub>CCA</sub>	٧	
		CONTROL FILL OF	1.40 to 1.65				.35xV <sub>CCA</sub>		
	Low -Level Input		1.10 to 1.40				.10xV <sub>CCA</sub>		
	Voltage			2.70 to 3.60			.80		
				2.30 to 2.70			.70		
$V_{ILB}$			Data Inputs B <sub>n</sub>	1.10 to 3.60	1.65 to 2.30			.35xV <sub>CCB</sub>	٧
				1.40 to 1.65			.35xV <sub>CCB</sub>		
				1.10 to 1.40			.10xV <sub>CCB</sub>		
V <sub>OHA</sub>	High-Leyel Output	l <sub>OH</sub> =-4 μA	1.10 to 3.60	1.10 to 3.60	V <sub>CCA</sub> 4			.,	
V <sub>OHB</sub>	Voltage <sup>(3)</sup>	Ι <sub>ΟΗ</sub> =-4 μΑ	1.10 to 3.60	1.10 to 3.60	V <sub>CCB</sub> 4			V	
V <sub>OLA</sub>	Low -Level Output	loL=4 μA	1.10 to 3.60	1.10 to 3.60			.4	.,	
V <sub>OLB</sub>	Voltage <sup>(3)</sup>	l <sub>OL</sub> =4 μA	1.10 to 3.60	1.10 to 3.60			.4	V	
		V <sub>IN</sub> =0.8 V	3.00	3.00	75.0				
		V <sub>IN</sub> =2.0 V	3.00	3.00	-75.0				
		V <sub>IN</sub> =0.7 V	2.30	2.30	45.0				
		V <sub>IN</sub> =1.6 V	2.30	2.30	-45.0				
	I <sub>I(HOLD)</sub> Bus-Hold Input Minimum Drive Current	V <sub>IN</sub> =0.57 V	1.65	1.65	25.0				
l(HOLD)		V <sub>IN</sub> =1.07 V	1.65	1.65	-25.0			μΑ	
		V <sub>IN</sub> =0.49 V	1.40	1.40	11.0				
			V <sub>IN</sub> =0.91 V	1.40	1.40	-11.0			
		V <sub>IN</sub> =0.11 V	1.10	1.10		4.0			
		V <sub>IN</sub> =0.99 V	1.10	1.10		-4.0			

#### Note:

Continued on following page...

<sup>3.</sup> This is the output voltage for static conditions. Dynamic drive specifications are given in the Dynamic Output Electrical Characteristics table.

## DC Electrical Characteristics (Continued)

T<sub>A</sub>=-40 to 85°C.

Symbol	Parameter	Condition	V <sub>CCA</sub> (V)	V <sub>CCB</sub> (V)	Min.	Max.	Unit
			3.60	3.60	450.0		
	Bus-Hold Input		2.70	2.70	300.0		
I(ODH)	Overdrive High	Data Inputs A <sub>n</sub> , B <sub>n</sub>	1.95	1.95	200.0		μΑ
	Current <sup>(4)</sup>		1.60	1.60	120.0		
			1.40	1.40	80.0		
			3.60	3.60	-450.0		
	Bus-Hold Input		2.70	2.70	-300.0		
I <sub>I(ODL)</sub>	Overdrive Low	Data Inputs A <sub>n</sub> , B <sub>n</sub>	1.95	1.95	-200.0		μΑ
	Current <sup>(5)</sup>		1.60	1.60	-120.0		
			1.40	1.40	-80.0		
l <sub>l</sub>	Input Leakage Current	Control Inputs OE, VI=VCCA or GND	1.10 to 3.60	3.60		±1.0	μΑ
	Pow er-Off Leakage	$A_n V_O=0 V to 3.6 V$	0	3.60		±2.0	
loff	Current	B <sub>n</sub> V <sub>O</sub> =0 V to 3.6 V	3.60	0		±2.0	μA
	$A_n$ , $B_n$ $V_O=0$ $V$ or $3.6$ $V$ , $OE=V_{IL}$		3.60	3.60		±5.0	
loz	3-State Output Leakage	An V <sub>O</sub> =0 V or 3.6 V, OE=V <sub>CCA</sub>	3.60	0		±5.0	μΑ
		B <sub>n</sub> V <sub>O</sub> =0 V or 3.6 V, OE=3.6V	0	3.60		±5.0	
lcca/B	Quiescent Supply Current 6' 7'	V <sub>I</sub> =V <sub>CCI</sub> or GND; l <sub>O</sub> =0, OE=V <sub>IH</sub>	1.10 to 3.60	1.10 to 3.60		10.0	μΑ
lccz	Current <sup>(6</sup> , 7)	V <sub>I</sub> =V <sub>CCI</sub> or GND; l <sub>O</sub> =0, OE=GND	1.10 to 3.60	1.10 to 3.60		10.0	μΑ
ICCA		V <sub>I</sub> =V <sub>CCB</sub> or GND; l <sub>O</sub> =0 B-to-A Direction; OE=V <sub>IH</sub>	0	1.10 to 3.60		-10.0	μА
	Quiescent Supply Current	V <sub>I</sub> =V <sub>CCA</sub> or GND; I <sub>O</sub> =0 A-to-B Direction	1.10 to 3.60	0		10.0	
Іссв		V <sub>I</sub> =V <sub>CCA</sub> or GND; l <sub>O</sub> =0, A-to-B Direction, OE=V <sub>IH</sub>	1.10 to 3.60	0		-10.0	μΑ
		V <sub>I</sub> =V <sub>CCB</sub> or GND; I <sub>O</sub> =0 B-to-A Direction	0	1.10 to 3.60		10.0	

#### Notes:

- 4. An external drive must source at least the specified current to switch LOW-to-HIGH.
- 5. An external drive must source at least the specified current to switch HIGH-to-LOW.
- 6. V<sub>CCI</sub> is the V<sub>CC</sub> associated with the input side.
  7. Reflects current per supply, V<sub>CCA</sub> or V<sub>CCB</sub>.

## **Dynamic Output Electrical Characteristic**

A Port (A<sub>n</sub>)

Output Load:  $C_L=15$  pF,  $R_L \ge M\Omega$  ( $C_{I/O}=4$  pF),  $T_A=-40$  to  $85^{\circ}C$ 

Symbol	Parameter	V <sub>CCA</sub> =3.0 V to 3.6 V		V <sub>CCA</sub> =2.3 V to 2.7 V		V <sub>CCA</sub> =1.65 V to 1.95 V		V <sub>CCA</sub> =1.4 V to 1.6 V		V <sub>CCA</sub> =1.1 V to 1.3 V	Unit
		Тур.	Max.	Тур.	Max.	Тур.	Max	Тур.	Max.	Тур.	
t <sub>rise</sub>	Output Rise Time A Port <sup>(9)</sup>		3.0		3.5		4.0		5.0	7.5	ns
t <sub>fall</sub>	Output Fall Time A Port <sup>(10)</sup>		3.0		3.5		4.0		5.0	7.5	ns
Юна	Dynamic Output Current High <sup>(</sup> 9 <sup>)</sup>	-11.4		-7.5		-4.7		-3.2		-1.7	mA
Юц	Dynamic Output Current Low <sup>(10)</sup>	+11.4		+7.5		+4.7		+3.2		+1.7	mA

## B Port (B<sub>n</sub>)

Output Load:  $C_L=15$  pF,  $R_L \ge M\Omega$  ( $C_{I/O}=5$  pF),  $T_A=-40$  to  $85^{\circ}C$ 

Symbol	Parameter	V <sub>CCB</sub> =3.0 V to 3.6 V		V <sub>CCB</sub> =2.3 V to 2.7 V		V <sub>CCB</sub> =1.65 V to 1.95 V		V <sub>CCB</sub> =1.4 V to 1.6 V		V <sub>CCB</sub> =1.1 V to 1.3 V	Unit
	Тур.	Max.	Тур.	Max.	Тур.	Max	Тур.	Max.	Тур.		
t <sub>rise</sub>	Output Rise Time B Port <sup>(9)</sup>		3.0		3.5		4.0		5.0	7.5	ns
t <sub>fall</sub>	Output Fall Time B Port <sup>(10)</sup>		3.0		3.5		4.0		5.0	7.5	ns
Юна	Dynamic Output Current High <sup>(9)</sup>	-12.0		-7.9		-5.0		-3.4		-1.8	mA
ЮЦД	Dynamic Output Current Low <sup>(10)</sup>	+12.0		+7.9		+5.0		+3.4		+1.8	mA

#### Notes:

- 8. Dynamic output characteristics are guaranteed, but not tested.9. See Figure 7.
- 10. See Figure 8.

## **AC** Characteristics

## $V_{CCA} = 3.0 \text{ V to } 3.6 \text{ V}, T_A = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter				V <sub>CCB</sub> =2.3 V to 2.7 V		V <sub>CCB</sub> =1.65 V to 1.95 V		=1.4 V .6 V	V <sub>CCB</sub> =1.1 V to 1.3 V	Unit
		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
tplH,tpHL	A to B	0.2	4.0	0.3	4.2	0.5	5.4	0.6	6.8	6.9	ns
IPLH, IPHL	B to A	0.2	4.0	0.2	4.1	0.3	5.0	0.5	6.0	4.5	ns
t <sub>PZL</sub> ,t <sub>PZH</sub>	OE to A, OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port <sup>(11)</sup>		0.5		0.5		0.5		1.0	1.0	ns

## $V_{CCA} = 2.3 \text{ V to } 2.7 \text{ V}, T_A = -40 \text{ to } 85^{\circ}\text{C}$

Symbol Paramete		V <sub>CCB</sub> =3.0 V to 3.6 V		V <sub>CCB</sub> =2.3 V to 2.7 V		V <sub>CCB</sub> =1.65 V to 1.95 V		V <sub>CCB</sub> =1.4 V to 1.6 V		V <sub>CCB</sub> =1.1 V to 1.3 V	Unit
		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
tou tou	A to B	0.2	4.1	0.4	4.5	0.5	5.6	0.8	6.9	7.0	ns
t <sub>PLH</sub> ,t <sub>PHL</sub>	B to A	0.3	4.2	0.4	4.5	0.5	5.5	0.5	6.5	4.8	ns
t <sub>PZL</sub> ,t <sub>PZH</sub>	OE to A, OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port <sup>(11)</sup>		0.5		0.5		0.5		1.0	1.0	ns

## $V_{CCA} = 1.65 \text{ V to } 1.95 \text{ V}, T_A = -40 \text{ to } 85^{\circ}\text{C}$

Symbol Paramete		V <sub>CCB</sub> =3.0 V to 3.6 V		V <sub>CCB</sub> =2.3 V to 2.7 V		V <sub>CCB</sub> =1.65 V to 1.95 V		V <sub>CCB</sub> =1.4 V to 1.6 V		V <sub>CCB</sub> =1.1 V to 1.3 V	Unit
		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
t <sub>PLH</sub> ,t <sub>PHL</sub>	A to B	0.3	5.0	0.5	5.5	0.8	6.7	0.9	7.5	7.5	ns
IPLH, IPHL	B to A	0.5	5.4	0.5	5.6	0.8	6.7	1.0	7.0	5.4	ns
t <sub>PZL</sub> ,t <sub>PZH</sub>	OE to A, OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port <sup>(11)</sup>		0.5		0.5		0.5		1.0	1.0	ns

#### Note

11. Skew is the variation of propagation delay between output signals and applies only to output signals on the same port (An or Bn) and switching with the same polarity (LOW-to-HIGH or HIGH-to-LOW) (see Figure 10). Skew is guaranteed, but not tested.

## AC Characteristics (Continued)

## $V_{CCA} = 1.4 \text{ V to } 1.6 \text{ V}, T_A = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter		=3.0 V 3.6 V	V <sub>CCB</sub> =	=2.3 V 2.7 V	V <sub>CCB</sub> =	1.65 V 95 V	V <sub>CCB</sub> =	:1.4 V .6 V	V <sub>CCB</sub> =1.1 V to 1.3 V	Unit
		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
tplH,tpHL	A to B	0.5	6.0	0.5	6.5	1.0	7.0	1.0	8.5	7.9	ns
	B to A	0.6	6.8	0.8	6.9	0.9	7.5	1.0	8.5	6.1	ns
t <sub>PZL</sub> ,t <sub>PZH</sub>	OE to A, OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port <sup>(12)</sup>		1.0		1.0		1.0		1.0	1.0	ns

## $V_{CCA} = 1.1 \text{ V to } 1.3 \text{ V}, T_{A} = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter	to 3.6 V	to 2.7 V	V <sub>CCB</sub> =1.65 V to 1.95 V	to 1.6 V	V <sub>CCB</sub> =1.1 V to 1.3 V Typ.	Unit
		Тур.	Тур.	Тур.	Тур.		
<b>.</b>	A to B	4.6	4.8	5.4	6.2	9.2	ns
tplH,tpHL	B to A	6.8	7.0	7.4	7.8	9.1	ns
t <sub>PZL</sub> ,t <sub>PZH</sub>	OE to A, OE to B	1.7	1.7	1.7	1.7	1.7	μs
tskew	A Port, B Port <sup>(12)</sup>	1.0	1.0	1.0	1.0	1.0	ns

#### Note:

<sup>12.</sup> Skew is the variation of propagation delay between output signals and applies only to output signals on the same port (A<sub>n</sub> or B<sub>n</sub>) and switching with the same polarity (LOW-to-HIGH or HIGH-to-LOW) (see Figure 10). Skew is guaranteed, but not tested.

# Maximum Data Rate (13, 14)

#### T<sub>A</sub>=-40 to 85°C

V <sub>CCA</sub>	V <sub>CCB</sub> =3.0 V to 3.6 V	V <sub>CCB</sub> =2.3V to 2.7V	V <sub>CCB</sub> =1.65V to 1.95V	V <sub>CCB</sub> =1.4V to 1.6V	V <sub>CCB</sub> =1.1V to 1.3V	Unit
	Min.	Min.	Min.	Min.	Тур.	
V <sub>CCA</sub> =3.00 to 3.60 V	140	120	100	80	40	Mbps
V <sub>CCA</sub> =2.30 to 2.70 V	120	120	100	80	40	Mbps
V <sub>CCA</sub> =1.65 to 1.95 V	100	100	80	60	40	Mbps
V <sub>CCA</sub> =1.40 to 1.60 V	80	80	60	60	40	Mbps
V <sub>CCA</sub> =1.10 to 1.30 V	Тур.	Тур.	Тур.	Тур.	Тур.	
V CCA=1.10 to 1.50 V	40	40	40	40	40	Mbps

- Notes:

  13. Maximum data rate is guaranteed, but not tested.
  - 14. Maximum data rate is specified in megabits per second (see Figure 9). It is equivalent to two times the F-toggle frequency, specified in megahertz. For example, 100 Mbps is equivalent to 50MHz.

## Capacitance

Symbol	Parameter		Conditions	T <sub>A</sub> =+25°C Typical	Unit
C <sub>IN</sub>	Input Capacitance Control	Pin (OE)	V <sub>CCA</sub> =V <sub>CCB</sub> =GND	3	pF
C <sub>I/O</sub>	Input/Output Capacitance	An	V <sub>CCA</sub> =V <sub>CCB</sub> =3.3 V, OE=GND	4	PΓ
0,0	B <sub>n</sub>		V G G A - V G G B - G . G V , G L - G I V B	5	۲,
C <sub>pd</sub>	Pow er Dissipation Capacita	nce	$V_{CCA}$ = $V_{CCB}$ =3.3 $V$ , $V_{I}$ =0 $V$ or $V_{CC}$ , $f$ =10 MHz	25	pF

#### I/O Architecture Benefit

The FXLA0104 I/O architecture benefits the end user, beyond level translation, in the following three ways:

Auto Direction without an external direction pin.

**Drive Capacitive Loads**. Automatically shifts to a higher current drive mode only during "Dynamic Mode" or HL / LH transitions.

**Lower Power Consumption**. Automatically shifts to low-power mode during "Static Mode" (no transitions), lowering power consumption.

The FXLA0104 does not require a direction pin. Instead, the VO architecture detects input transitions on both side and automatically transfers the data to the corresponding output. For example, for a given channel, if both A and B side are at a static LOW, the direction has been established as A  $\rightarrow$  B, and a LH transition occurs on the B port; the FXLA0104 internal VO architecture automatically changes direction from A  $\rightarrow$  B to B  $\rightarrow$  A.

During HL / LH transitions, or "Dynamic Mode," a strong output driver drives the output channel in parallel with a weak output driver. After a typical delay of approximately 10 ns - 50 ns, the strong driver is turned off, leaving the weak driver enabled for holding the logic state of the channel. This weak driver is called the "bus

hold." "Static Mode" is when only the bus hold drives the channel. The bus hold can be over ridden in the event of a direction change. The strong driver allows the FXLA0104 to quickly charge and discharge capacitive transmission lines during dynamic mode. Static mode conserves power, where  $I_{CC}$  is typically  $< 5 \,\mu A$ .

#### **Bus Hold Minimum Drive Current**

Specifies the minimum amount of current the bus hold driver can source/sink. The bus hold minimum drive current ( $I_{HOLD}$ ) is  $V_{CC}$  dependent and guaranteed in the DC Electrical tables. The intent is to maintain a valid output state in a static mode, but that can be overridden when an input data transition occurs.

## **Bus Hold Input Overdrive Drive Current**

Specifies the minimum amount of current required (by an external device) to overdrive the bus hold in the event of a direction change. The bus hold overdrive ( $II_{ODH}$ ,  $II_{ODL}$ ) is  $V_{CC}$  dependent and guaranteed in the DC Electrical tables.

## **Dynamic Output Current**

The strength of the output driver during LH / HL transitions is referenced on page 8, Dynamic Output Electrical Characteristics. I<sub>OHD</sub>, and I<sub>OLD</sub>.

## **Test Diagrams**

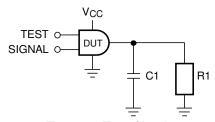


Figure 3. Test Circuit

Table 1. AC Test Conditions

Test	Input Signal	Output Enable Control
tplH, tpHL	Data Pulses	VCCA
tpzL	0V	LOW to HIGH Switch
tрzн	V <sub>CCI</sub>	LOW to HIGH Switch

## Table 2. AC Load

V <sub>cco</sub>	C1	R1
1.2 V± 0.1 V	15 pF	1 MΩ
1.5 V± 0.1 V	15 pF	1 MΩ
1.8 V ± 0.15 V	15 pF	1 MΩ
2.5 V ± 0.2 V	15 pF	1 MΩ
3.3 V ± 0.3 V	15 pF	1 MΩ

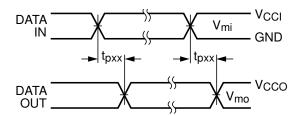


Figure 4. Waveform for Inverting and Non-Inverting Functions

#### Notes:

- 15. Input  $t_R = t_F = 2.0$  ns, 10% to 90%.
- 16. Input  $t_R = t_F = 2.5$  ns, 10% to 90%, at  $V_I = 3.0$  V to 3.6 V only.

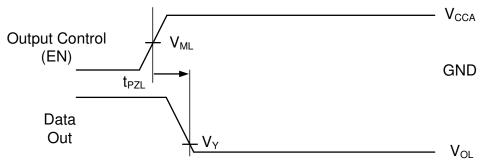


Figure 5. 3-State Output Low Enable

#### Notes:

- 17. Input  $t_R = t_F = 2.0$  ns, 10% to 90%.
- 18. Input  $t_R = t_F = 2.5$  ns, 10% to 90%, at  $V_I = 3.0$  V to 3.6 V only.

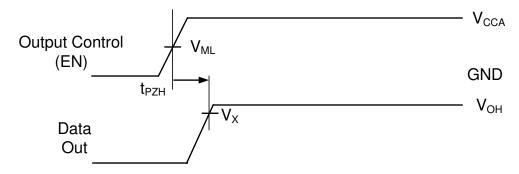


Figure 6. 3-State Output High Enable

## Notes:

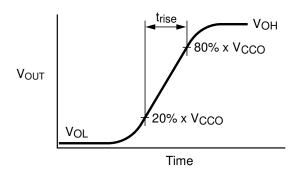
- 19. Input  $t_R = t_F = 2.0 \text{ ns}$ , 10% to 90%.
- 20. Input  $t_R = t_F = 2.5$  ns, 10% to 90%, at  $V_I = 3.0$  V to 3.6 V only.

Table 3. Test Measure Points

Symbol	$V_{ exttt{DD}}$
V <sub>MI</sub> <sup>(21)</sup>	V <sub>CCI</sub> /2
V <sub>MO</sub>	V <sub>CCo</sub> /2
Vx	0.9 x V <sub>CCo</sub>
V <sub>Y</sub>	0.1 x V <sub>CCo</sub>

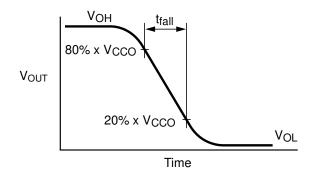
#### Note:

21. V<sub>CCI</sub>=V<sub>CCA</sub> for control pin OE or V<sub>MI</sub>(V<sub>CCA</sub>/2).



$$I_{OHD} \approx (C_L + C_{I/O}) \times \frac{\Delta V_{OUT}}{\Delta t} = (C_L + C_{I/O}) \times \frac{(20\% - 80\%) \bullet V_{CCO}}{t_{RISE}}$$

Figure 7. Active Output Rise Time and Dynamic Output Current High



$$I_{OLD} \approx (C_L + C_{I/O}) \times \frac{\Delta V_{OUT}}{\Delta t} = (C_L + C_{I/O}) \times \frac{(80\% - 20\%) \bullet V_{CCO}}{t_{FALL}}$$

Figure 8. Active Output Fall Time and Dynamic Output Current Low

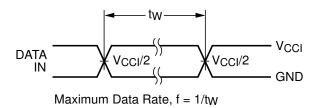


Figure 9. Maximum Data Rate

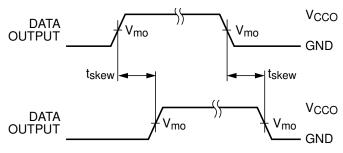
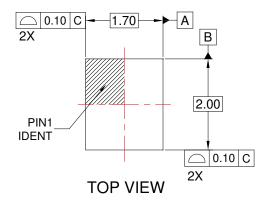


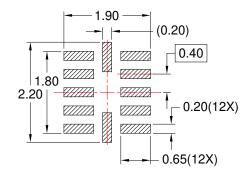
Figure 10. Output Skew Time

Note:

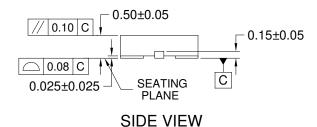
22.  $t_{SKEW} = (t_{pHLmax} - t_{pHLmin}) \text{ or } (t_{pLHmax} - t_{pLHmin})$ 

## **Physical Dimensions**



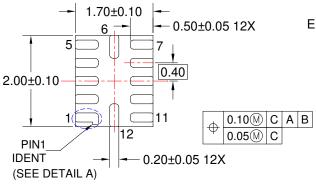


#### RECOMMENDED LAND PATTERN



## NOTES:

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO-220 REGISTRATION
  - B. DIMENSIONS ARE IN MILLIMETERS.
  - C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  - D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY.
  - E. DRAWING FILENAME: MKT-UMLP12Crev2.



0.50 0.25

DETAIL A

**BOTTOM VIEW** 

Figure 11. 12-Lead, Ultrathin Molded Leadless Package (UMLP)

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